

**SOT-23 BIPOLAR TRANSISTORS
TRANSISTOR(PNP)**

FEATURES

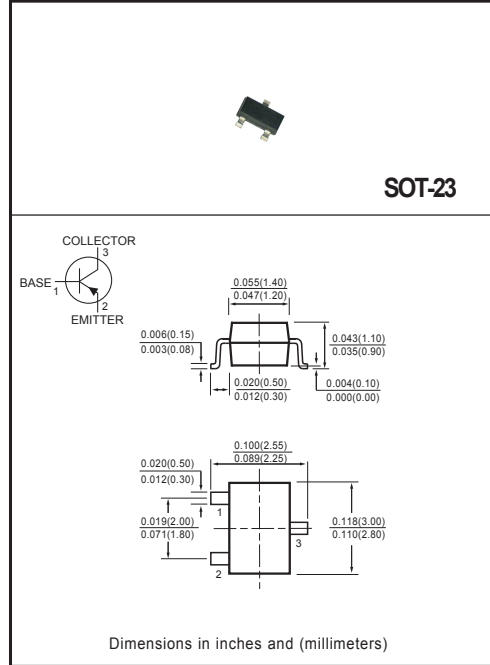
* Power dissipation

MECHANICAL DATA

* Case: Molded plastic
* Epoxy: UL 94V-O rate flame retardant
* Lead: MIL-STD-202E method 208C guaranteed
* Mounting position: Any
* Weight: 0.008 gram

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase , half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.



MAXIMUM RATINGS (@ TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	VALUE	UNITS
Collector-emitter voltage	V _{CBO}	-32	V
Collector-emitter voltage	V _{CEO}	-32	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current-continuous	I _C	-0.1	A
Power dissipation	P _C	0.25	W
Junction and storage temperature	T _J , T _{stg}	-55 - 150	°C

ELECTRICAL CHARACTERISTICS (@ TA = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL	MIN	TYP	MAX	UNITS
Collector-base breakdown voltage (I _C = -10μA, I _E =0)	V _{(BR)CBO}	-32	-	-	V
Collector-emitter breakdown voltage (I _C = -1mA, I _B =0)	V _{(BR)CEO}	-32	-	-	V
Emitter-base breakdown voltage (I _E = -10μA, I _C =0)	V _{(BR)EBO}	-5	-	-	V
Collector cut-off current (V _{CB} = -32V, I _E =0)	I _{CBO}	-	-	-0.02	μA
Collector cut-off current (V _{EB} = -4V, I _C =0)	I _{EBO}	-	-	-0.02	μA
DC current gain (V _{CE} = -5V, I _C = -10μA)	h _{FE}	30	-	-	-
DC current gain (V _{CE} = -5V, I _C = -2mA)		180	-	310	-
DC current gain (V _{CE} = -1V, I _C = -50mA)		80	-	-	-
Collector-emitter saturation voltage (I _C = -10mA, I _B = -0.25mA)	V _{CE(sat)}	-0.06	-	-0.25	V
Collector-emitter saturation voltage (I _C = -50mA, I _B = -1.25mA)	V _{CE(sat)}	-0.12	-	-0.55	V
Base-emitter saturation voltage (I _C = -10mA, I _B = -0.25mA)	V _{BE(sat)}	-0.6	-	-0.85	V
Base-emitter saturation voltage (I _C = -50mA, I _B = -1.25mA)		-0.68	-	-1.05	V
Base-emitter voltage (V _{CE} = -5V, I _C = -10μA)	V _{BE(ON)}	-	-0.55	-	V
Base-emitter voltage (V _{CE} = -5V, I _C = -2mA)		-0.6	-	-0.75	V
Base-emitter voltage (V _{CE} = -1V, I _C = -50mA)		-	-0.72	-	V
Transition frequency (V _{CE} = -5V, I _C = -10mA, f=100MHz)	f _T	100	-	-	MHz
Collector capacitance (V _{CB} = -10V, I _E = 0, f=1MHz)	C _c	-	4.5	-	pF
Emitter capacitance (V _{EB} = -0.5V, I _C = 0, f=1MHz)	C _e	-	11	-	pF

Marking	BB
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